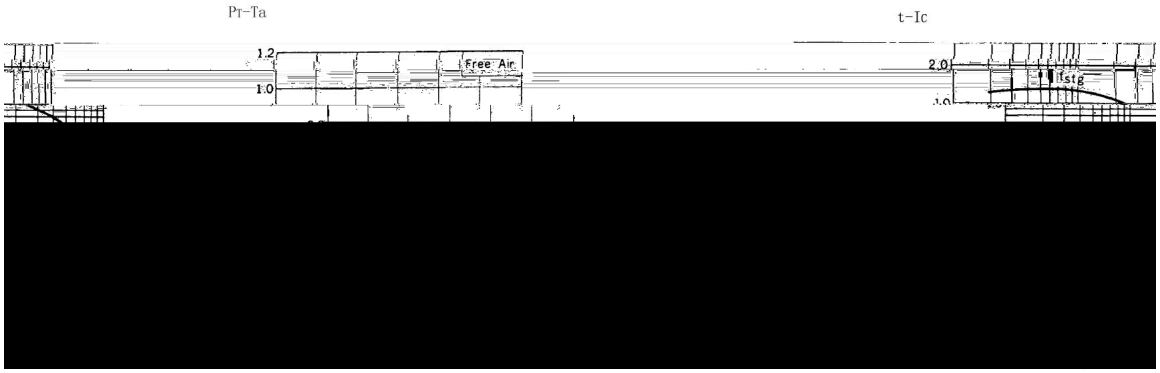
WR0<5 ḾḾÞ QSQ ÆṀ ч s ‖ ㄱ Silicon NPN transistor in a TO-92 Plastic Package.

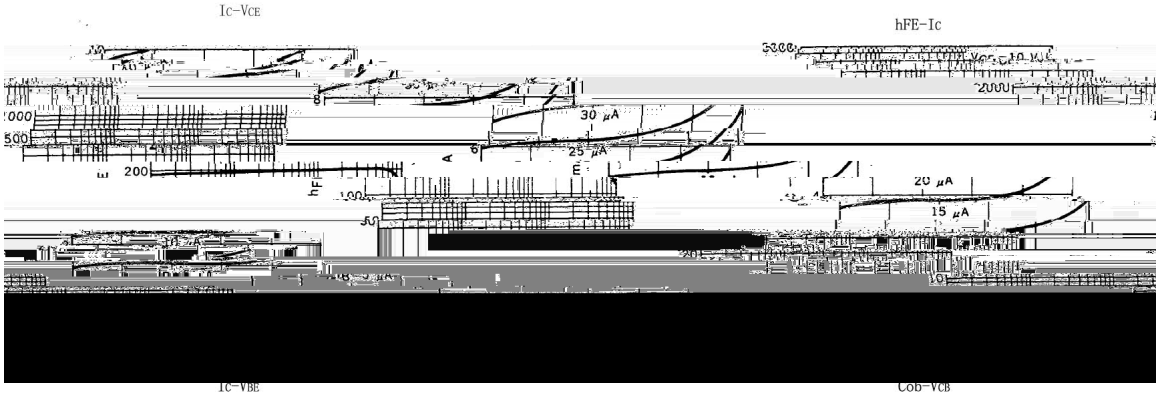
ㅊ ɔ я ı ѽ ᶻ ㅓ ớ Ḅ/ль 5VD46 : 9 Ѝ ´
High breakdown voltage, good h_{FE} linearity, complementary to 2SA1376.

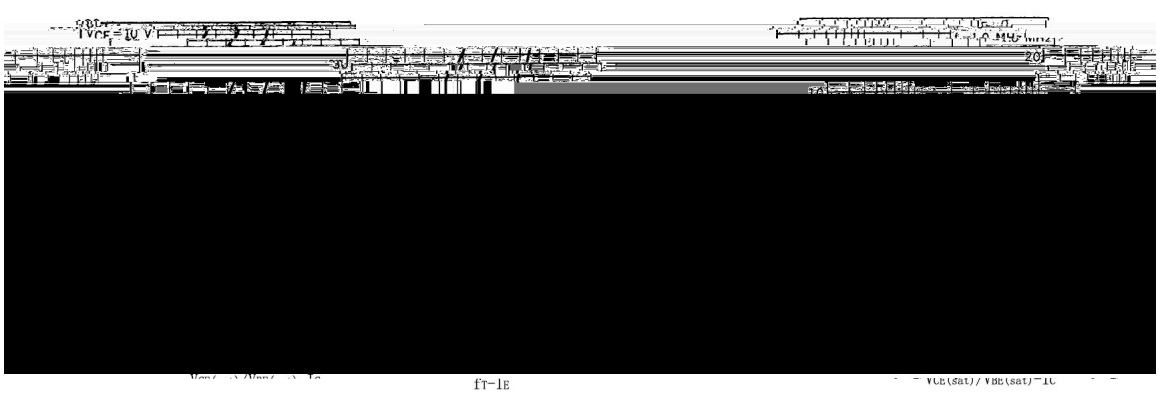
ᵷ̂ ⌊ ∂ ㅊ ɔ я ▯ ˇ ѽ ᶻ ɔ ت
General purpose amplifier applications requiring high breakdown voltages.

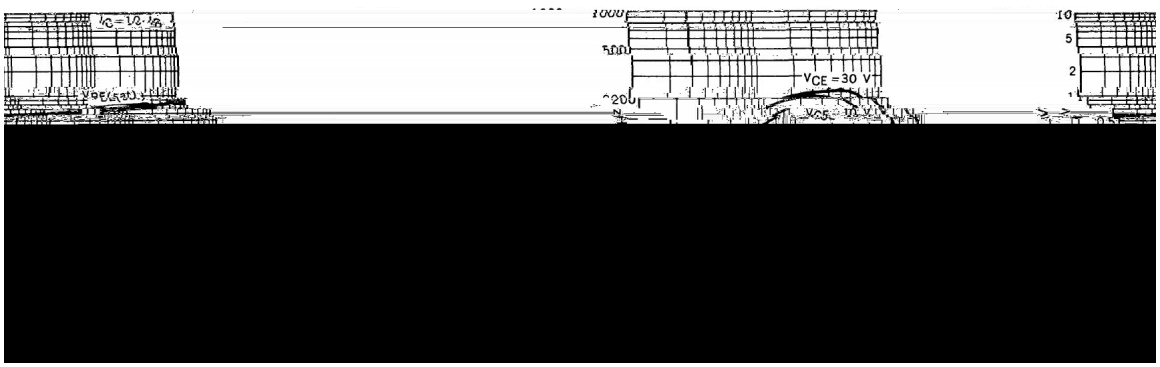
v ‴Ω Parameter	ϒ N Symbol	‴Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	180	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Current – Continuous(Pulse)	I_{CP}	200	mA
Base Current - Continuous	I_B	20	mA
Collector Power Dissipation	P_C	750	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T		

/ Electrical Characteristic Curve

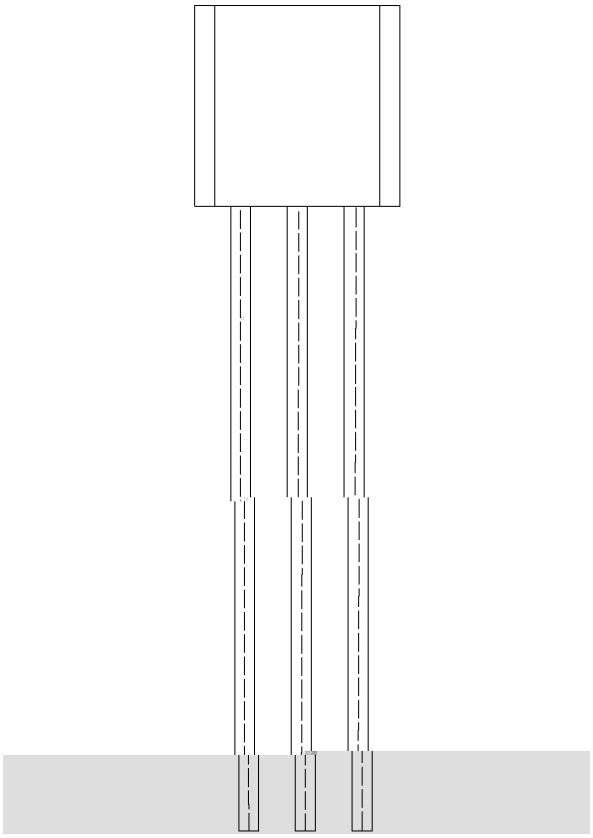






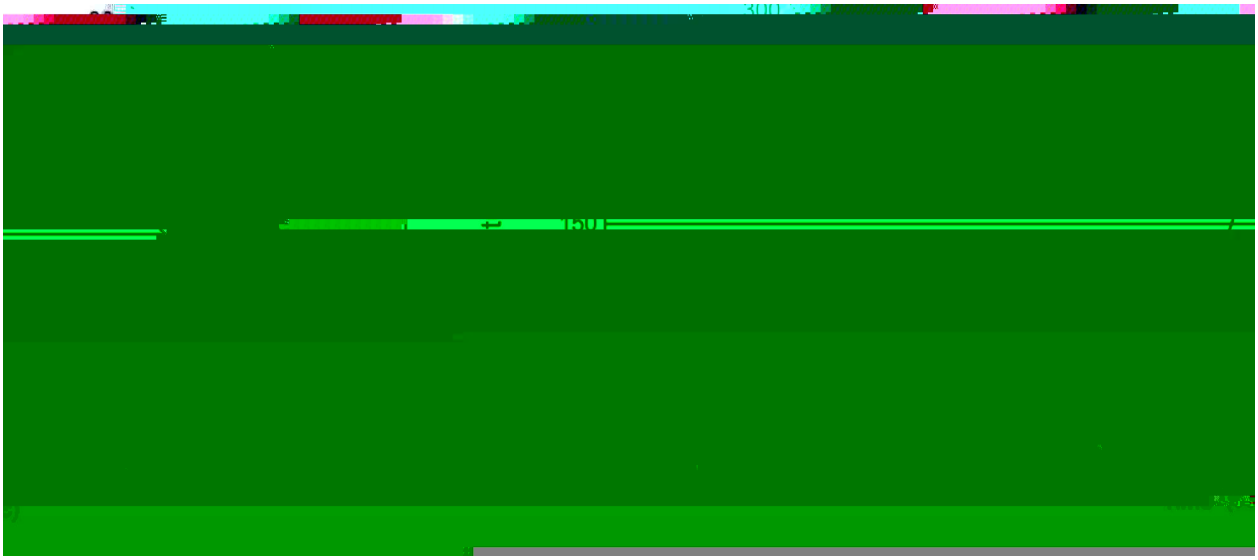


/ Marking Instructions



ب ˝ χ	
EU=	ѭ ϗ и Ґ
F67 : ; χ	ѭ ϳ N Ґ
0=	ѭ k IH ‘ 6 Ґ
---- χ	ѭ ı ғ ӈ N Ґ ı ֏ ı ғ ӈ N Ψ ק
Note:	
BR:	Company Code.
C3478:	Product Type.
0=	h

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ɬ ı ˋH ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ɬ ı ˋH ڑ ˋY ﾊ ᵿ 5 ° 0.5sec;

3 ì ˙ ϒ ˛ ɔ ﻉ ỷ ᵿ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:25~150 ɬ , Time:60~90sec.

2.Peak Temp.:255 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 270 ° 5 ɬ	ˋH ڑ χ 10 ° 1 sec.	Temp:270±5	Time:10±1 sec

/ Packaging SPEC.

ˈQ ţ ϒ Ł / BULK

Package Type	Units	Dimension	(unit mm3)